

EETimes Seminar- Circuit Protection for Power Management

Sept, 2017
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Agenda

- **Circuit Protection**
 - What is it ?
 - Where is it used ?
 - The Basic Parts
- **Device Features/Options**
 - Inrush, Fault, FET SOA Protection, OV, UV etc.
- **Common Design Errors**
- **Common Test Errors**

Circuit Protection – What is it ?

- **Many things with many names**

- Inrush Control
- Hotswap
- Hotplug
- **Current Limiting**
- Electronic Circuit Breaker
- **Short Circuit Protection**
- Soft Start
- **Over Voltage Protection (OVP)**
- eFuse

~ the same functions

- Load Power Limiting
- FET SOA Limiting (Protecting the Protector !)
- Reverse Current Protection (ORing)

- **Often Required for Agency Rating**

- **UL, CSA – North America**
- **EN, IEC, (CENELEC) – Europe**
- **CCC Mark (CNCA) - China**

Circuit Protection – *Where Is It Used ?*

- **Telecom Equipment**
- **Datacenters / Servers**
- **Storage / HDD, SSD, Midplanes**
- **Industrial Control**
 - 24 or 48 V typically
- **Tower Mounted Antennas**
- **Merchant Power**



Circuit Protection – What is it ?

- **Circuits designed specifically to....**
 - Prevent Fire ! --*“Keep the smoke in!”*
 - Keep small problems from growing big
 - Minimize damage by quickly isolating failures
 - Prevent potentially disruptive power bus disturbances
 - One small transient can take down/reset an entire system
- ***What Gets Protected ?***

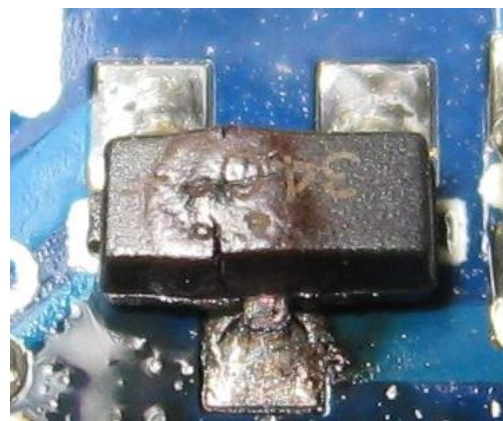
SUPPLY



CONNECTORS



POWER FET



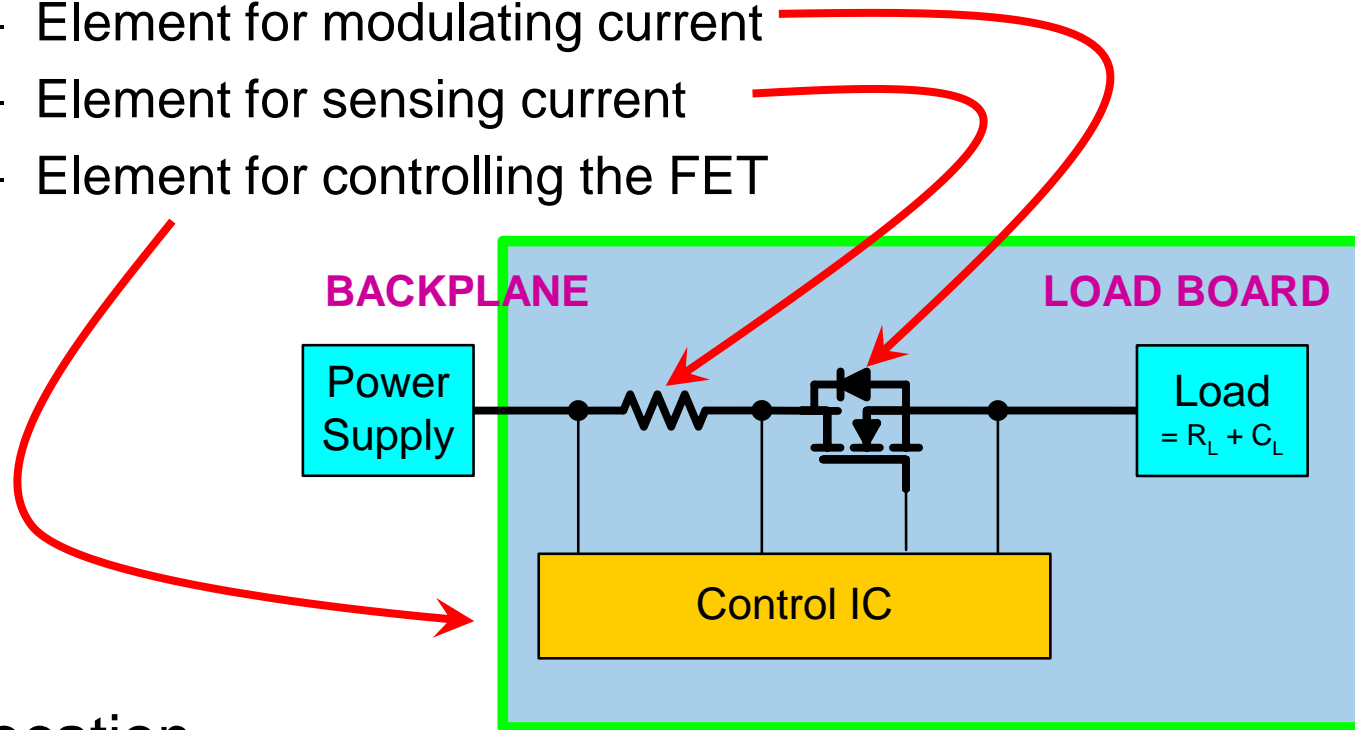
LOAD



Circuit Protection – The Basic Parts

- Most Common Elements

- Element for modulating current
- Element for sensing current
- Element for controlling the FET

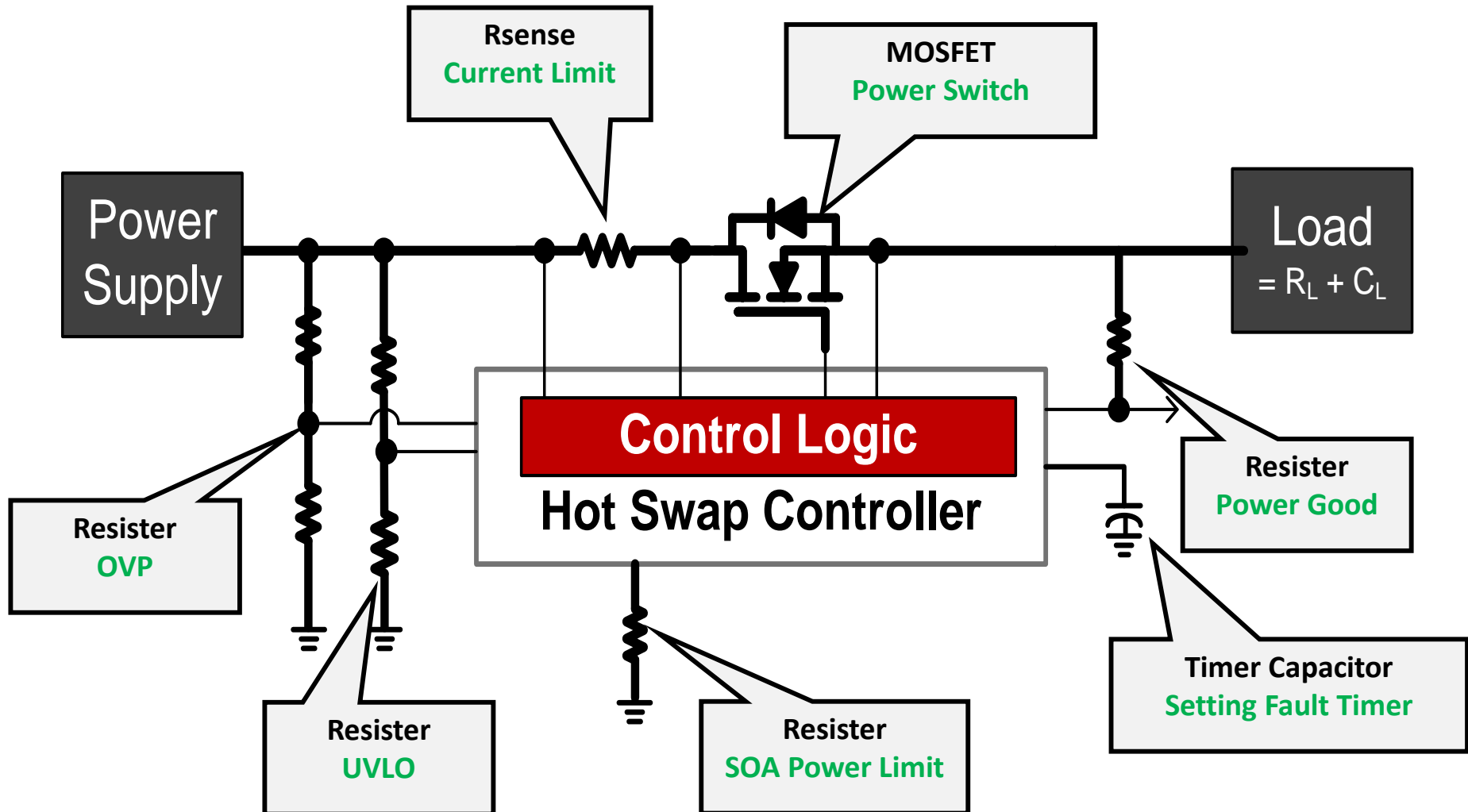


- Location..

- Sometimes on the Load Side of the Connector
- Sometimes on the Supply Side of the Connector

Hot Swap Controller Circuit

- Function



Device Features/Options

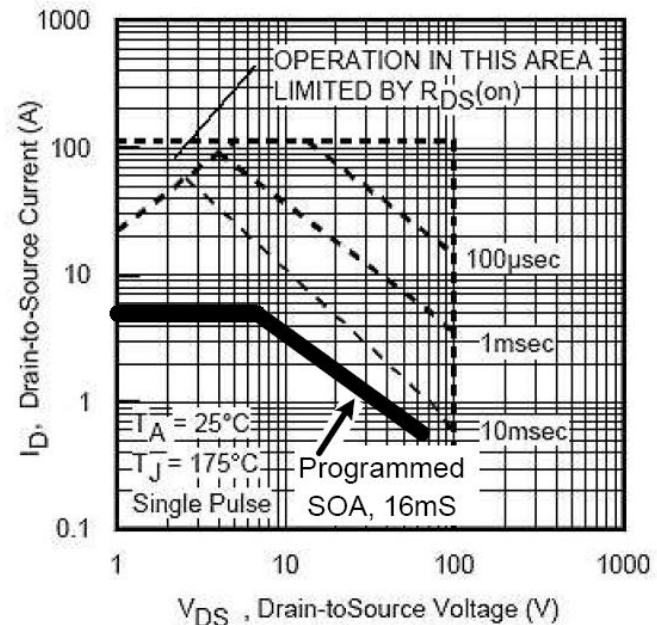
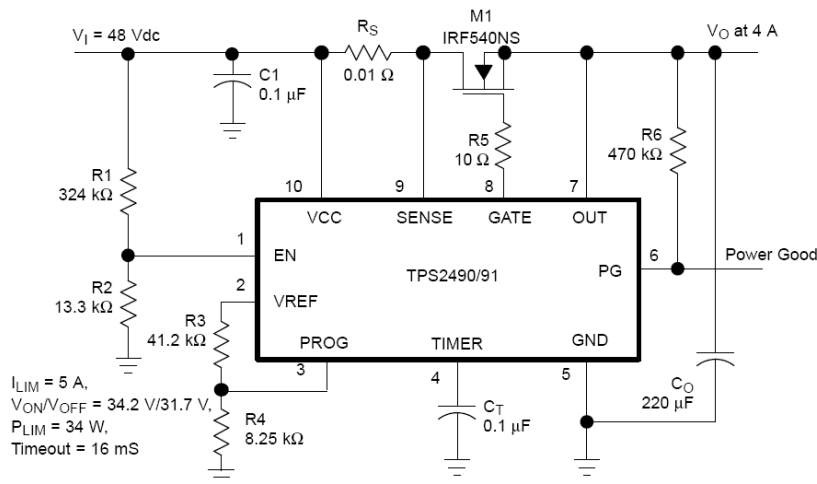
Some of the Choices

- FET - Internal or External
- Inrush control - dV/dT , or di/dT
- **Current Limit - Always, Never, or just at startup**
- Fault response - Latch off or Retry
- Short Circuit Response – Latch Off or Retry
- Control - I²C or Analog Control
- Outputs - Power Good, Fault, FET Fault
- I_{LIMIT} Accuracy - 20% Standard, 10% Pretty Good, 5% Very Good
- **FET SOA protection.. Or not**
 - **Allows use of smaller FET and provides very high survivability**
- Current Indicator Output (IMON) – Analog or Digital Output ?
 - Digital Output requires internal ADC and typically includes PIV Monitoring
- ORing Control – Linear or Hysteretic

Device Features/Options

FET SOA Protection

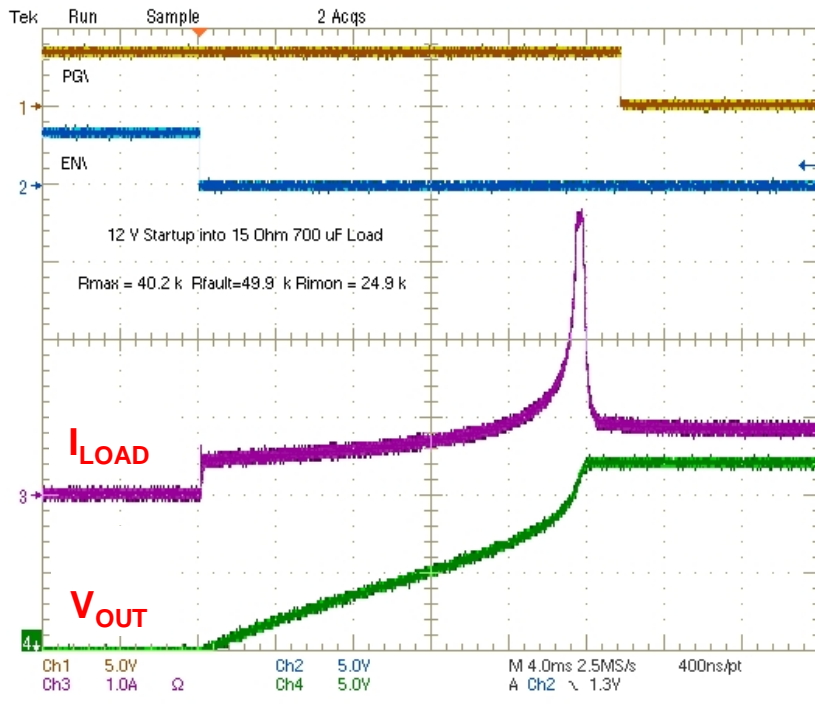
- One of the least understood but most appreciated features
- **Allows use of smaller, less expensive FETs**
- Analog multiplier calculates P_{DIS_FET} in real time and compares result to PROG pin
- **If $P_{LOAD} > PROG$ then gate drive reduced to lower I_{LOAD} and P_{FET}**



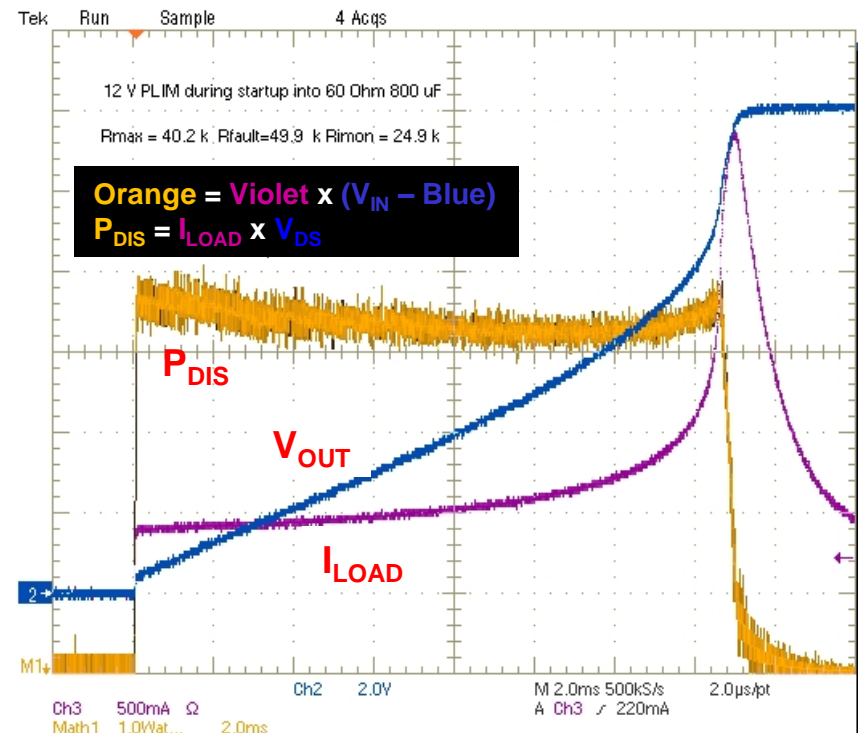
Device Features/Options

FET SOA Protection

- Dynamically adjusts I_{LIMIT} to be approximately proportional to $1/(V_{DS})^2$
- Limits P_{DIS} of fet to programmed limit



TPS2420 Startup into 15 Ω , 700 μ F

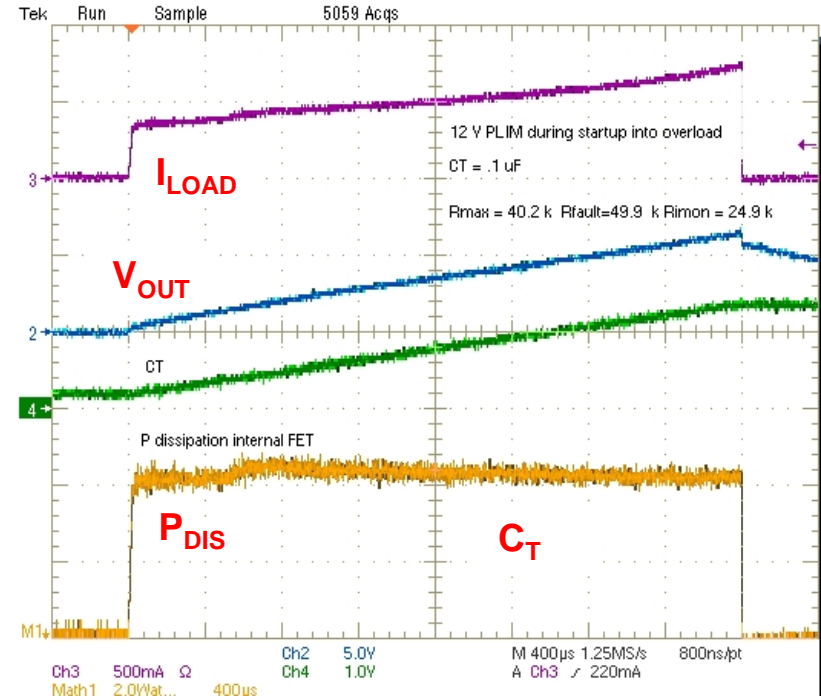


TPS2420 Limits FET $P_{DIS} < 5$ Watts

Device Features/Options

FET SOA Protection – Startup into overload

- SOA protection keeps FET safe even when starting up into a severe overload
- Fault timer limits T(ime) factor of SOA
- Some competitive devices will reduce I_{LIMIT} over a limited range and with limited protection.



TPS2420 Startup into overload

Typical Inrush/OCP Design Steps

1. Select R_{SENSE} to set I_{LIMIT} and I_{FASTTRIP}

- $I_{\text{LIMIT}} = V_{\text{TH}}/R_{\text{SENSE}} - V_{\text{TH}}$ typically 25 – 50 mV
 - Simplest controllers have fixed V_{TH}
 - *High $V_{\text{TH}} \rightarrow$ Better Accuracy but Higher I^2R Losses*
- Fast trip – (Short Circuit) threshold usually 1.5x -3x I_{LIMIT} Level

2. Select C_{FAULT} to get desired T_{FAULT}

- Set T_{FAULT} long enough to allow all caps to charge (T_{CHARGE}) before time out
 - $T_{\text{CHARGE}} \sim CV/I$ (C = Bulk Cap, V = V_{OUT} , I = I_{LIMIT})
- Set T_{FAULT} as short as possible to limit FET stress during overcurrent events
- Ensure that $T_{\text{FAULT}} \times V_{\text{IN}} \times I_{\text{LIMIT}}$ is within SOA curve

3. Select FET that can withstand $T_{\text{FAULT}} \times V_{\text{IN}} \times I_{\text{LIMIT}} \times \sim 1.5$ SOA !!

4. Set FET SOA Power Limit on devices so equipped

- **Design tools** available for some devices - check webpage
- *TPS24700/10/20, TPS2490/1/2/3, TPS2480/1, LM5064/6/7/9, LM25061/6/9*

Common Design Errors

1. *SOA of FET too Small*

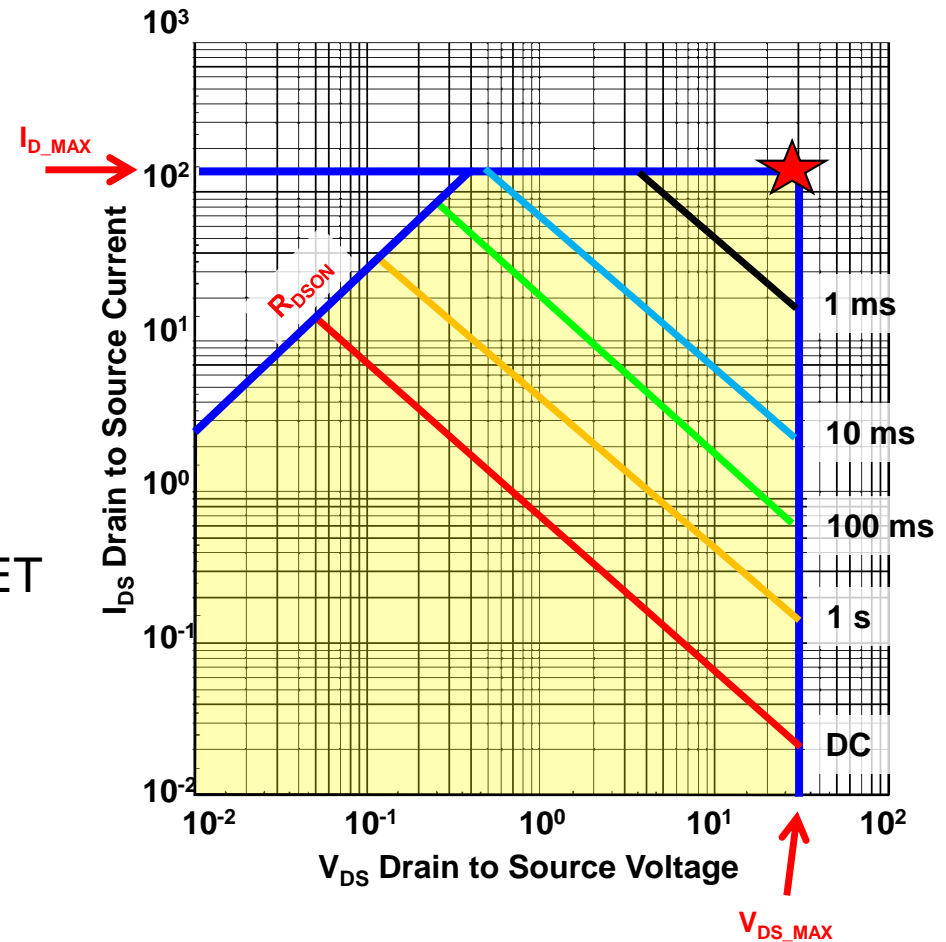
2. *Layout Issues*

3. *Inadequate Transient Protection*

Common Design Errors

SOA of FET Too Small

- **SOA = Safe Operating Area**
 - SOA Chart – Every FET has one
 - Defines Bounds of FET Operation
 - V_{DS_MAX} = Vertical Limit
 - I_{D_MAX} = Horizontal Limit
 - $R_{DS(ON)}$ limits I_D at lower voltages
 - **Theoretical** $P_{MAX} = 3000\text{ W}$
- **Fault Time Is Critical**
 - Longer Fault time means bigger FET
 - Shorter Fault Time allows higher peak power
- **Most Stressful FET Events**
 - Startup into short
 - Shorted load while under full load



Common Design Errors

SOA of FET Too Small - Example - 12 V, 50 A Server

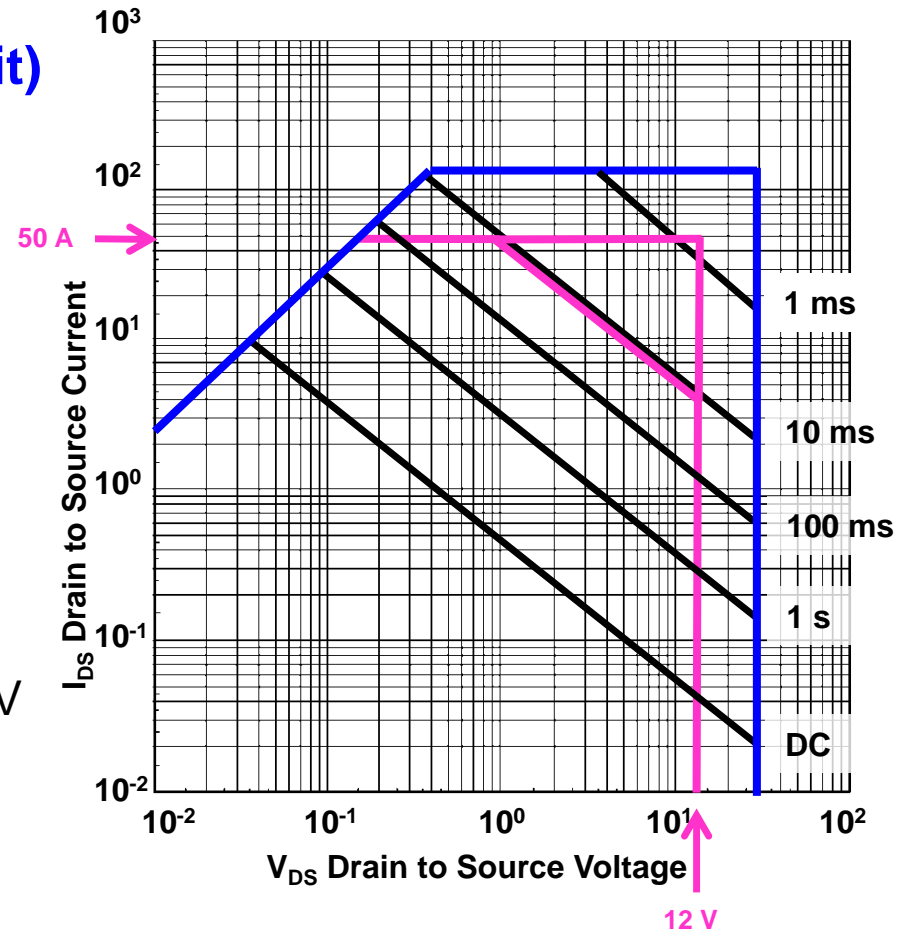
- Without Power Limiting(current limit)

- $P_{MAX} = I_{LIMIT} \times V_{SUPPLY} = 600 \text{ W}$
- $T_{SOA_MAX} = \sim 800 \text{ us}$

- With Power Limiting

- $P_{MAX_LIMITED} = 50 \text{ W}$
- As V_{DS} increases I_{LIMIT} is reduced
- $T_{SOA_MAX} = 10 \text{ ms}$
- Smaller FET can be used
- @ 50 A will start limiting when $V_{DS} > 1\text{V}$

- Common Error to Pick FET Too Small



Common Design Errors

Layout Issues - A Little Stray R Can Make a Big Error

- **Critical Kelvin Connections**

- Sense Runs

- **Critical Short Run**

- Ground
- Gate

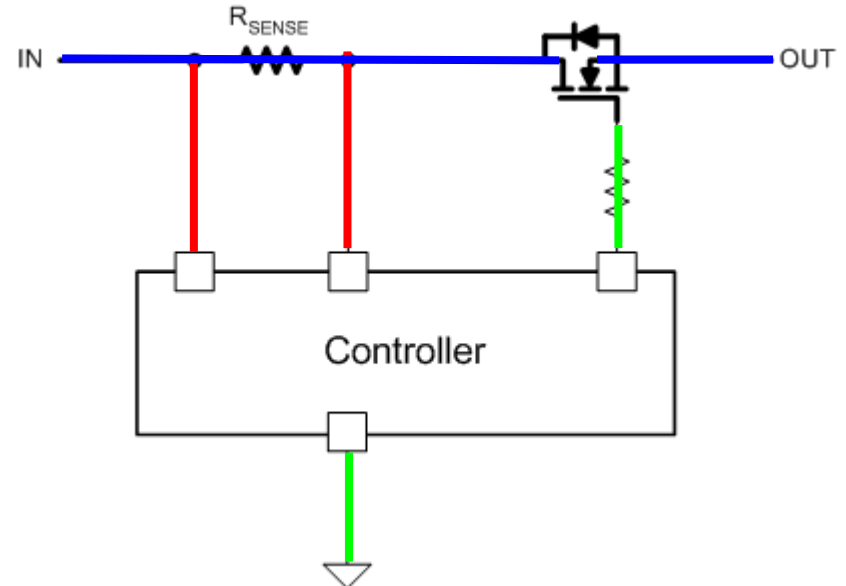
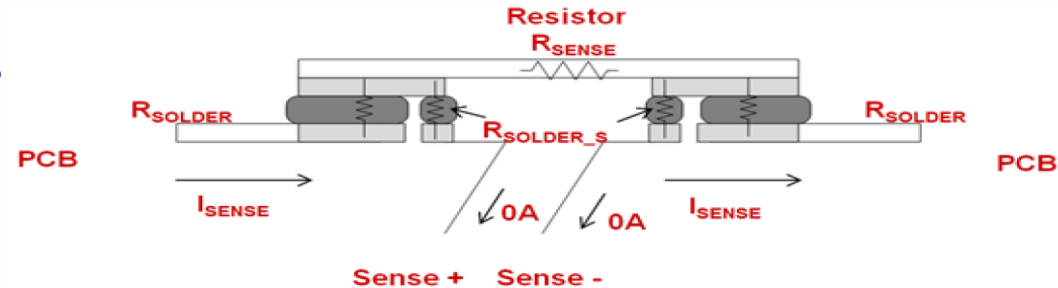
- **High Current Runs**

- **Poor Kelvin Runs...**

- Inaccurate/variable I_{LIMIT}

- **Poor High Current Runs**

- Voltage droop
- Power loss
- Overheating



Common Design Errors

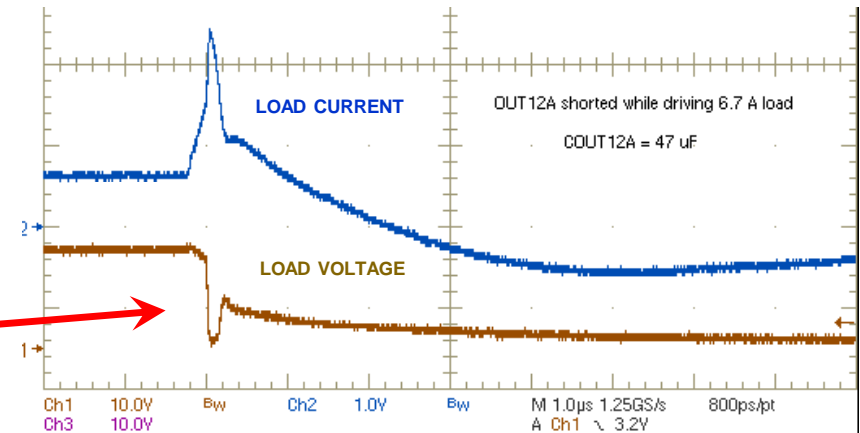
Inadequate Transient Protection

- All wires are inductive
- Inductance stores energy $E = \frac{LI^2}{2}$
- When the FET turns off, voltage spikes occur

$$V = L \frac{di}{dt} \quad \frac{di}{dt} \Rightarrow \infty$$

Positive Spikes at Input to Switch/FET

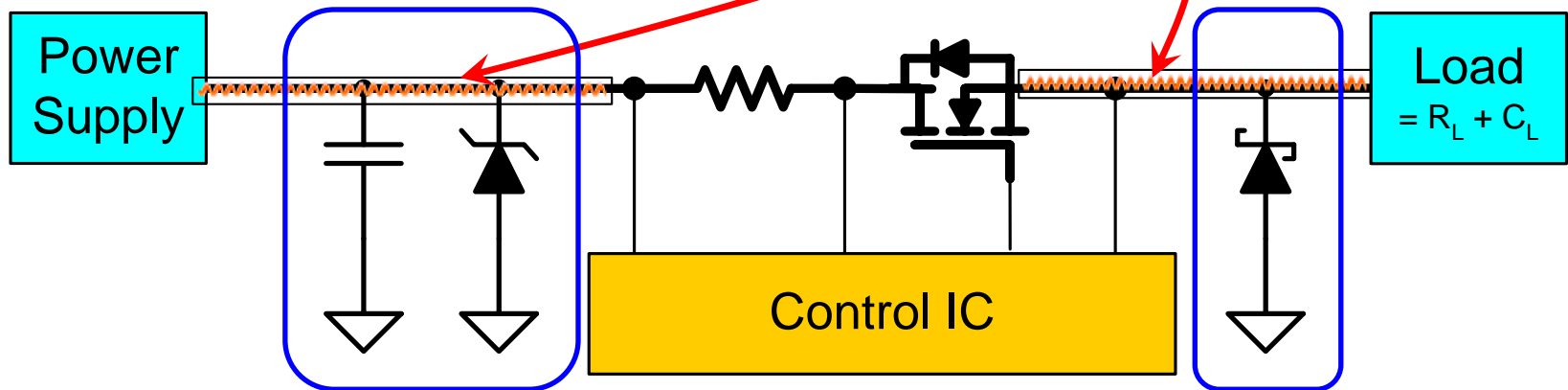
Negative Spikes at Output of Switch/FET



Common Design Errors

Inadequate Transient Protection

- To resolve inductive spikes from supply / load leads
 - Caps and/or TVS at Input to clamp positive spike during hot plug
 - Schottky Clamp output negative spike during output short circuit
 - Short, Wide Leads and Runs



Common Test Error Sources

1. *Electronic Loads*



2. *Transients From Long Supply Leads*



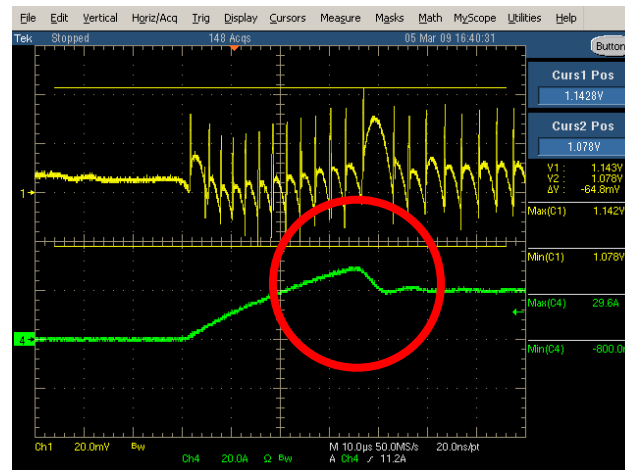
3. *Supply I_{LIMIT} Too Low*



Common Test Error Source 1

Electronic Loads

- Electronic Loads
 - Good for DC Loading and Automated Tests
 - Proper Setup Very Important
 - Ex. - Constant Current, Constant Power, Constant Resistance
 - but....
 - Often Have Switch Transients When Stepping Load
 - Transients Can Cause Premature Trip When Measuring I_{LIMIT}



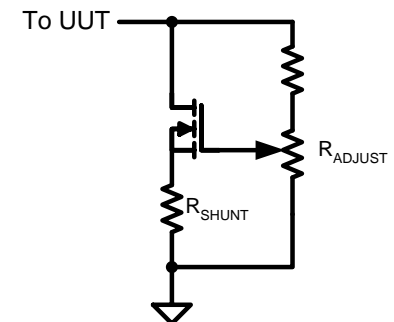
Common Test Error Source 1

Electronic Loads

- For Minimal Transients While Adjusting Load
 - **Method One** - Use Power Resistors as Loads
 - A bit tedious and Old School... but accurate
 - A collection of fixed and variable resistors is best
 - Apply “Last Half Amp” With Small Wire Rheostat
 - Can be effective with eLoads also



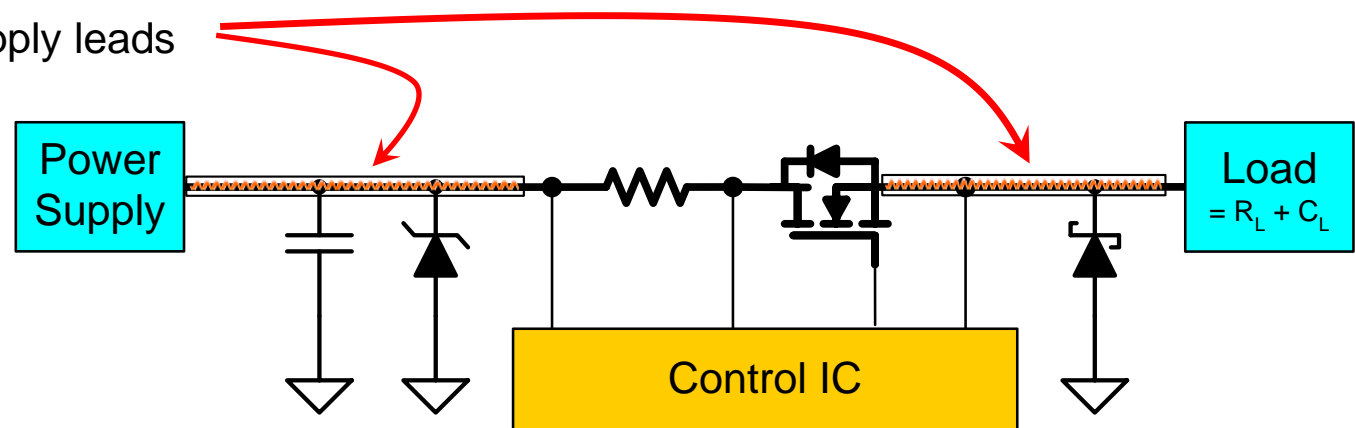
- **Method Two** - Use Power FET as Load
 - Connect FET and Series Resistor as Load
 - Adjust Potentiometer to vary Current
 - **Make Sure the FET can Handle the power !!!!**



Common Test Error Source 2

Long Supply Leads

- All wires are inductive
- Long Supply Leads can have significant L
- Lab Test Environment Usually Worse Than Final Application !
 - Reason for TVS and diodes on most TI EVMs
- When the FET turns off, voltage spikes occur
- To counter inductive spikes from supply / load leads
 - Caps and/or TVS at UUT Input to clamp positive spike
 - Schottky Clamp across output to clamp negative spike
 - Twisted Supply leads



Positive Low Voltage Protection

TI Device Portfolio

PART	Input Range	Package	V _{THRESH} (mV)	SOA Prot.	OV	I2C	PG	Imon Acc.
TPS2420	3 to 20	QFN16 (4x4mm)	Internal FET R _{DSON} typ. = 30 mΩ I _{LIMIT} = ±10% @ 2 A	Yes	No	No	Lo	17%@2A
TPS2590/910		QFN16 (4x4mm)		Yes	No	No	-	na
TPS2421-1/2		SOIC8		Yes	No	No	Lo	na
TPS2592A/B		QFN10 (3x3 mm)	na	No	Yes	No	No	na
TPS2593A/B			Fixed Ilimit	No	Yes	No		na
TPS24720	2.5 to 18	QFN16 (3x3)	Prog	Yes	Yes	No	Lo	Prog
TPS24710/1/2/3		MSOP10	25 ± 10%	Yes	No	No	l/l/h/h	na
TPS24700/1		MSOP8		No	No	No	Lo	na
LM25066	2.9 to 17	LLP24 (4x5mm)	25 ± 10% 46.5 ± 11.8%	Yes	Yes	Yes	Hi	2.40%
LM25066A/i		LLP24 (4x5mm)		Yes	Yes	Yes	Hi	1.00%
LM25069-1/2		MSOP10	50 ± 10%	Yes	Yes	No	Hi	na
LM25061-1/2		MSOP10	50 ± 10%	Yes	No	No	Hi	Na
TPS2480/1	9 to 26	PW20	25	Yes	No	Yes	Hi	1%
TPS2482/3	9 to 36	PW20	25	Yes	No	Yes	Hi	0.5%

Device Features/Options

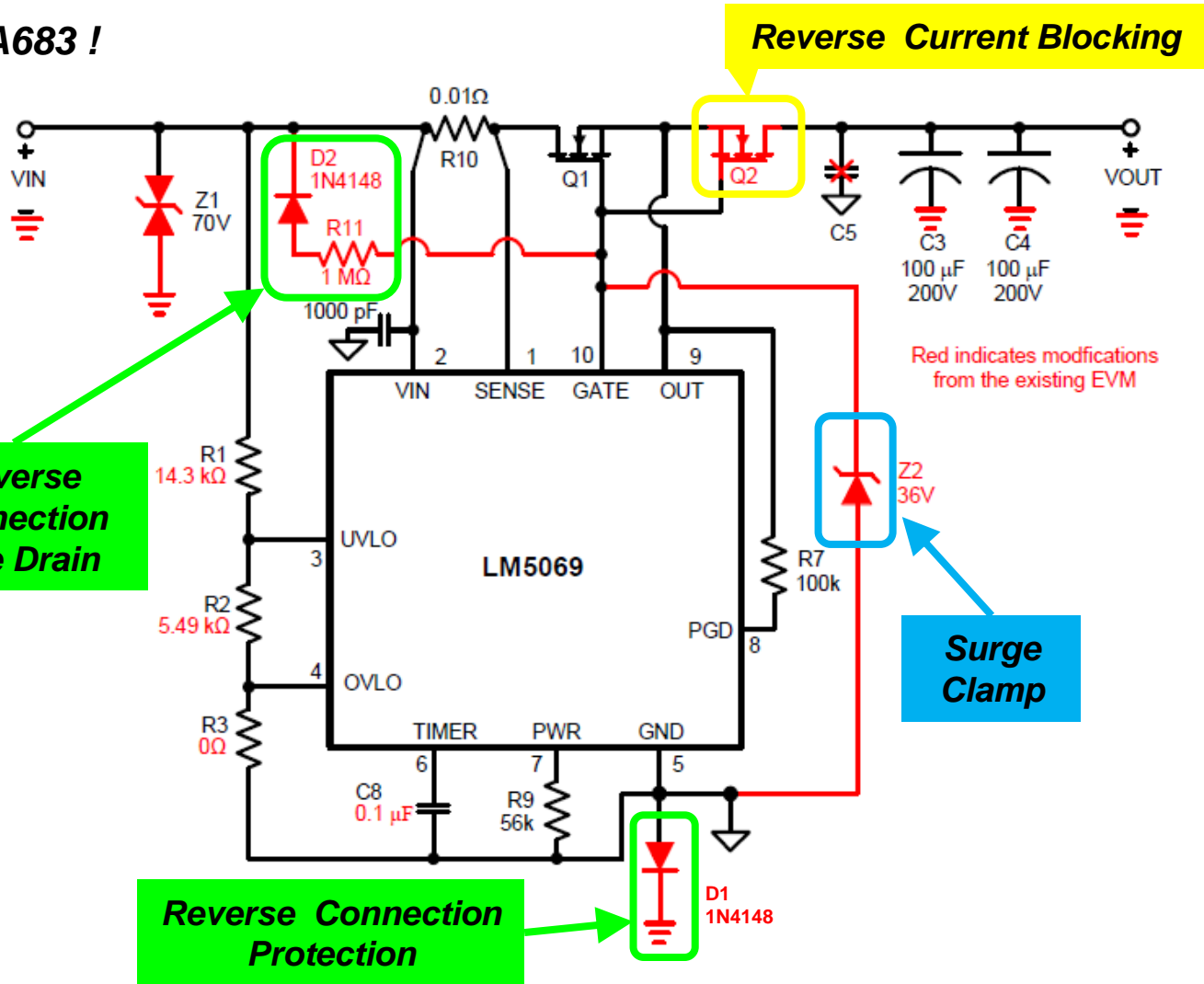
TI IMON Devices vs. Output Type

Part	V _{IN}	Current Monitor Output	Accuracy Neglecting external component tolerances
TPS2358/9 TPS2458/9 TPS2456	8.5 – 17 V	$I_{LOAD} = \frac{V_{MON} I_{LIMIT}}{675mV}$	± 4% _{FS}
TPS2420	2.8 – 20 V	$I_{LOAD} = I_{MON} \times 61000$	± 8.2%
TPS2492/3	9 – 80 V	$I_{LOAD} = \frac{V_{MON}}{48 \times R_{SENSE}}$	± 6%
LM25066/A	2.9 – 17 V	PMBus Output	± 2.4% _{FS} / ± 1% _{FS}
LM5064	-80 to -18	PMBus Output	± 3% _{FS}
LM5066	10 to 80	PMBus Output	± 3% _{FS}
TPS2480/1	9 – 26 V	Digital I ² C Output	± 1%

LM5069EVM-627

Reverse Current Blocking, Surge Clamping, Reverse Connection Protection

Take me to SNVA683 !

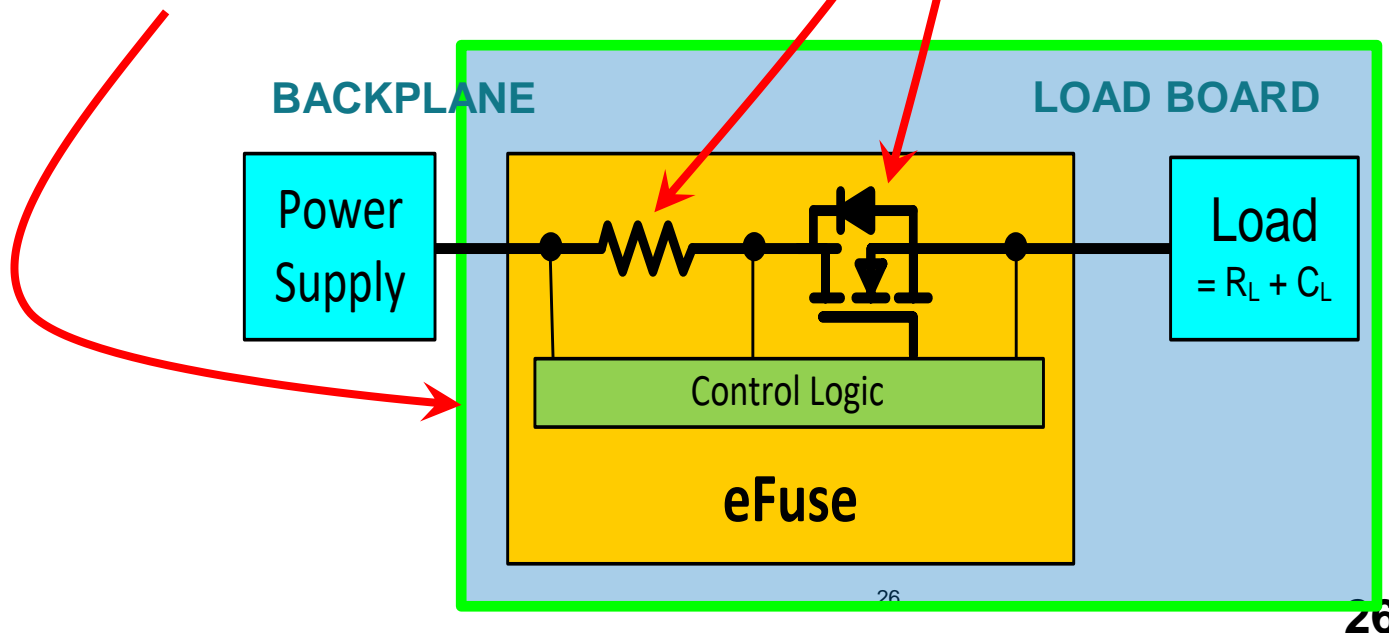


These circuits will also work with TPS248x/9x parts

What is an eFuse: Integrated Hotswap IC

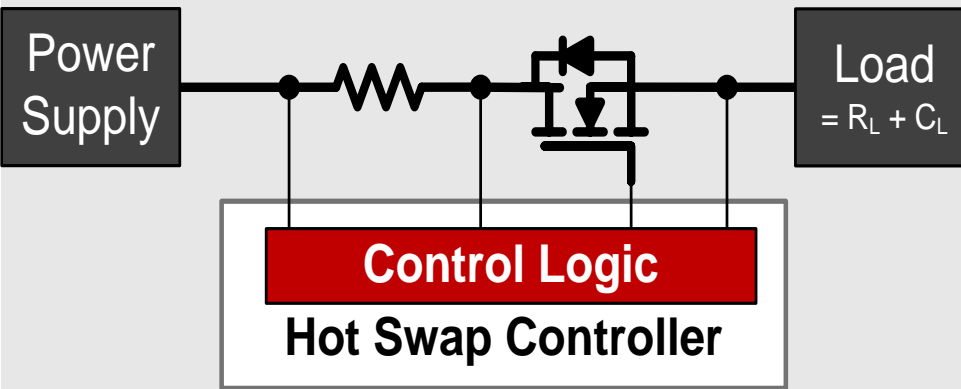
- **Most Common Elements:**

- Element for modulating current
- Element for sensing current
 - (R_{SENSE} shown, usually senseFET)
- Element to control the FET



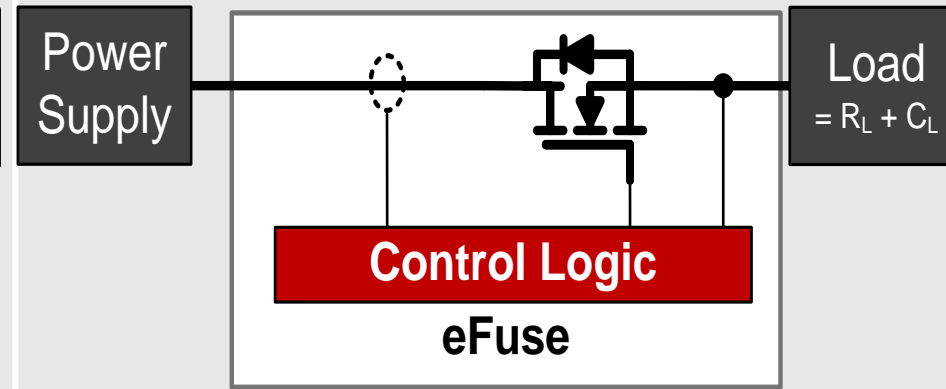
Hot Swap VS eFuse

Hot Swap (Desecrated MOSFET)



- Flexible R_{DSON} (Designers Choice)
- More feature options
 - No limit on upper current limit
 - Generally more accurate
- More external parts
 - R_{SENSE} , FET
 - R_s , C_s for configuration

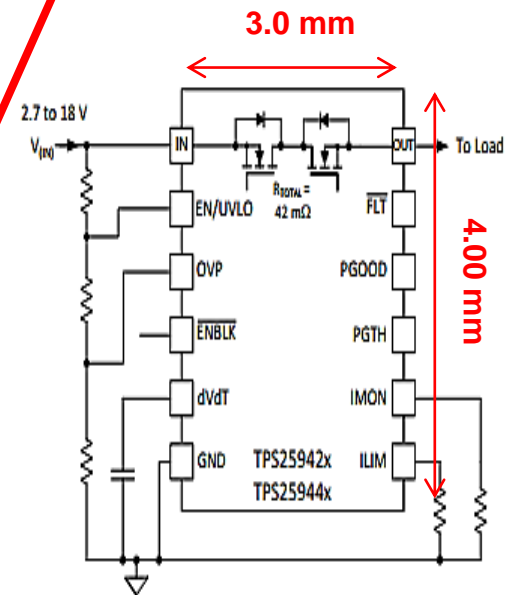
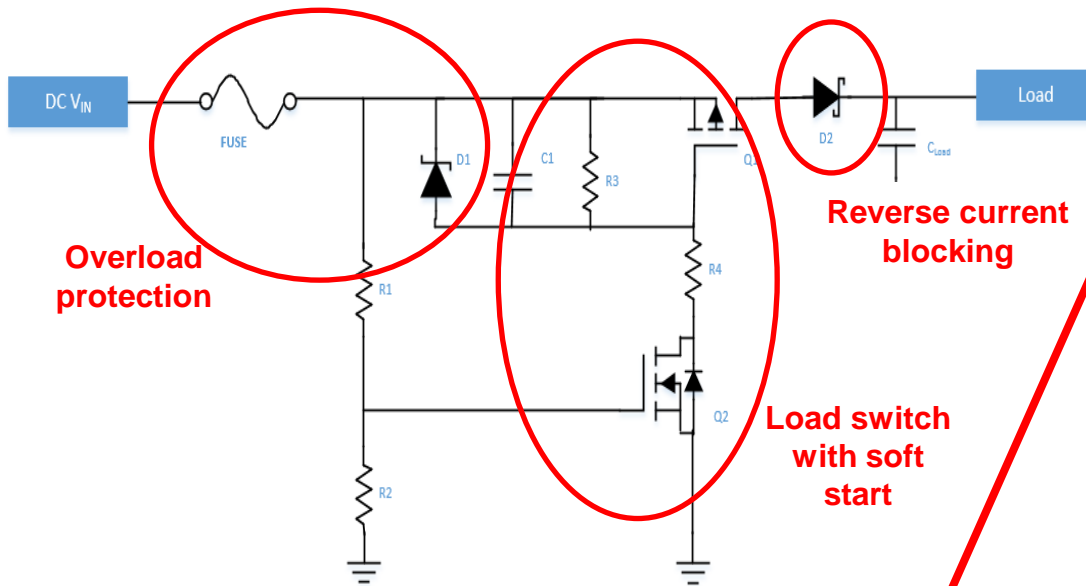
eFuse (Integrated MOSFET)



- Highly integrated
 - Few external parts
 - Internal FET, Current Sense
 - Thermal protection
 - Matched FET & protection
- Today , support < 10 A (18V)
support < 55 V (2A)

Discrete Fuse Protection Circuit

Replace all these components...



...with 1 eFuse.

Typical Applications for eFuse



m-SATA SSD



SAS HDD

Enterprise Class SSD



Storage Server
Chassis



Set-Top Box
DVD Player
Internet TV

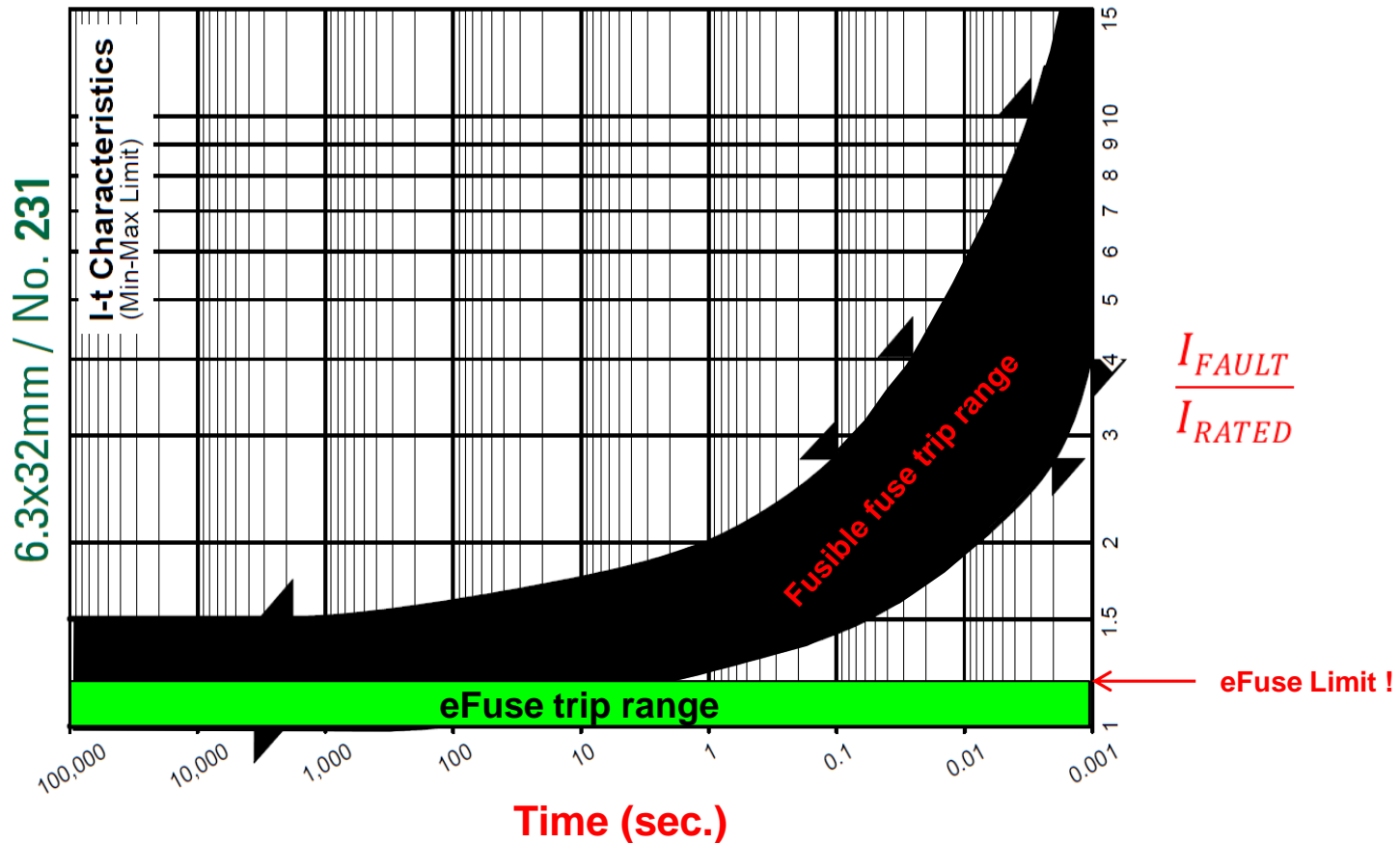


Appliances

Why not use a fuse ?

- **Slow**
- **Inaccurate**
- **Lossy**
- **Leave a load unpowered after event**

“Fast Blo Fuse ” Trip time vs Current eFuse vs fuse



- Time and trip limit inaccuracies mean bigger power supplies

Fuses are sloweven the fast ones




Limits for Pre-arcing Time					
Rated Current	$1.0 \times I_N^1$	$1.5 \times I_N$	$2.75 \times I_N$	$4 \times I_N$	$10 \times I_N$
2.00 A ... 16.00 A	> 1 h	< 30 min	2 ms ... 100 ms	1 ms ... 25 ms	< 3 ms

eFuse Performance

- I_{LIMIT} is programmable, predictable, and stable over temp
- Bus droop and supply stress reduced by tight over current tolerance

Fuses are Lossy

- Higher resistance -> more energy -> more heat -> **higher OPEX**
- 13x more power lost with fuse !**
 - 800 mV/2A = **400 mΩ vs. eFuse @ 30 m Ω**
- Lifetime cost of 1 Watt = \$2 to \$18 (customer supplied numbers)
 - Includes energy cost, distribution infrastructure, HVAC, product life

Rated Current	Amp Code	Voltage Rating	Voltage Drop $1.0 \times I_N$  max. (mV)	Power Dissipation $1.0 \times I_N$  max. (W)	Melting Integral $10 \times I_N$  max. (A ² s)
2.00 A	1200	500 V	800	3.0	0.35
2.50 A	1250	500 V	800	3.0	0.44
3.15 A	1315	500 V	800	3.0	0.75
4.00 A ²	1400	500 V	700	3.6	1.6
5.00 A ²	1500	500 V	600	3.6	2.5
6.30 A ²	1630	500 V	600	3.6	5
8.00 A ²	1800	500 V	600	5.2	10
10.00 A ²	2100	500 V	500	5.2	20
12.50 A ²	2125	500 V	500	6.3	38
16.00 A ^{1,2}	2160	500 V	480	6.3	68

Lower Losses using TPS2590 (30 mΩ)

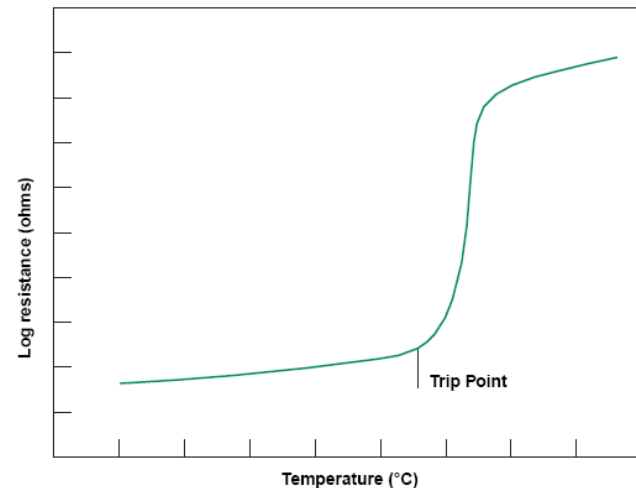
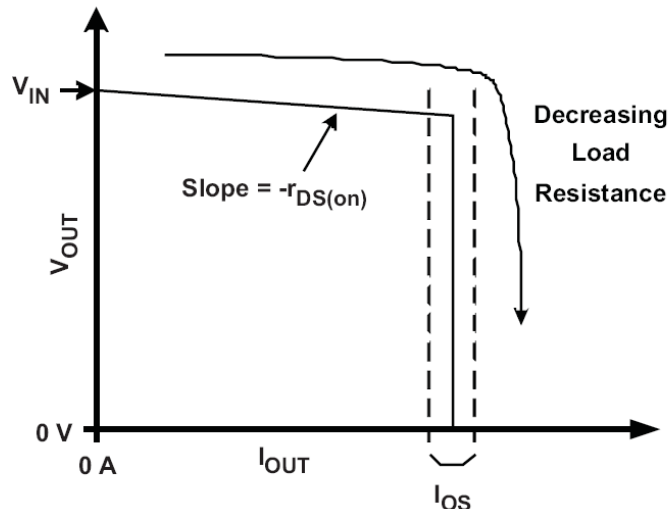
eFuse vs. Polyfuse

- **eFuse (USB power switch)**

- **Current based I_{LIMIT}**
- **Stable, accurate (20% - 30%) I_{LIMIT}**
- **Fixed or Programmable I_{LIMIT}**
- **Repeatable I_{LIMIT}**
- **Fast ($< 1.5 \mu s$ typ)**
- **Wide temp range**
 - **-40° to $+125^\circ C^\circ$**

- **Polyfuse**

- **Temp based I_{LIMIT}**
- **Sloppy, variable I_{LIMIT}**
- **No Programmable I_{LIMIT}**
- **R_{ON} Increases with each event**
- **Slow to trip (several ms)**
- **Not usable above $85^\circ C^\circ$**
- **Auto –resets after trip event**



Polyfuses (PTC Devices)

Require derating

Temperature Derating Curves Comparing PTCs to Fuses

Chart Key

Curve A

Thin-Film Fuses and 313 Series (.010 to .150A)

Curve B

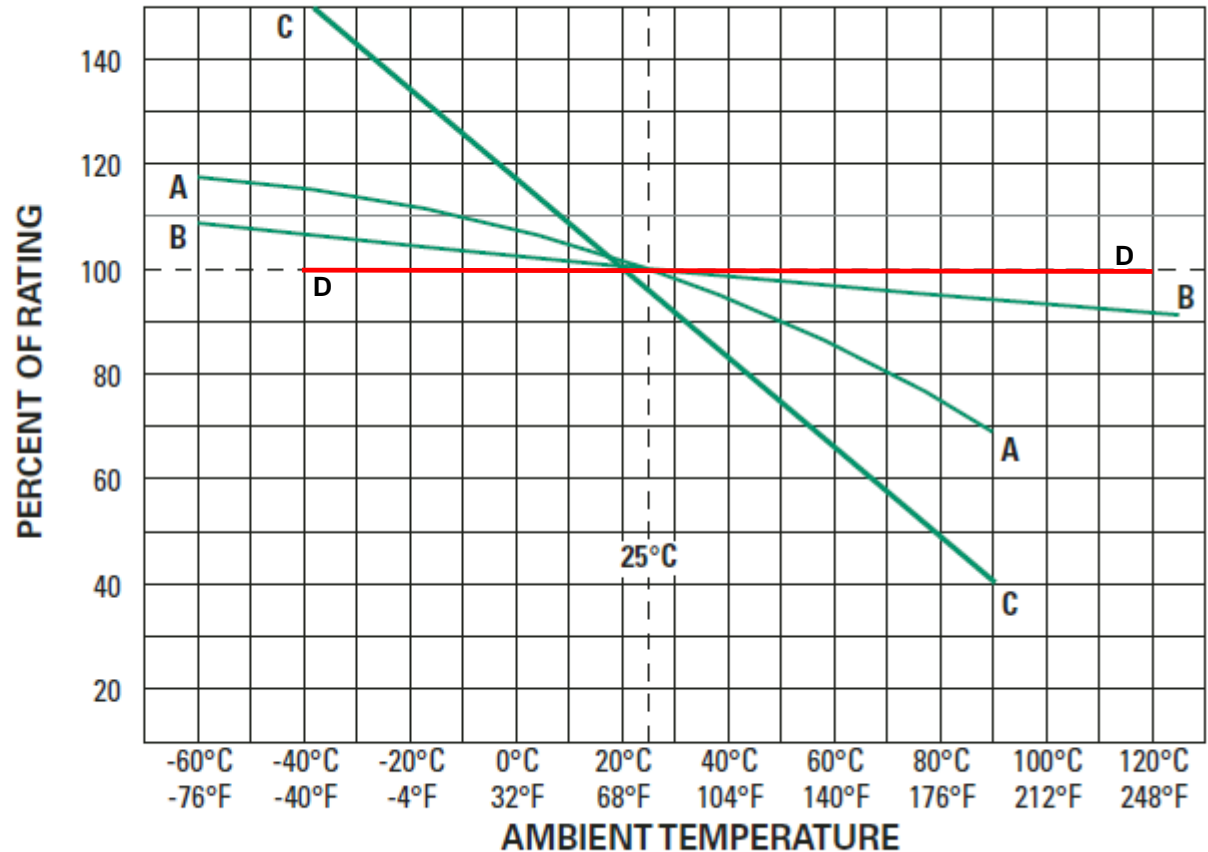
FLAT-PAK[®], Telelink[®], Nano²[®], PICO[®], Blade Terminal, Special Purpose and other leaded and cartridge fuses (except 313.010 – .150A)

Curve C

Resettable PTCs

Curve D

TPS2420/21,
TPS2590/910



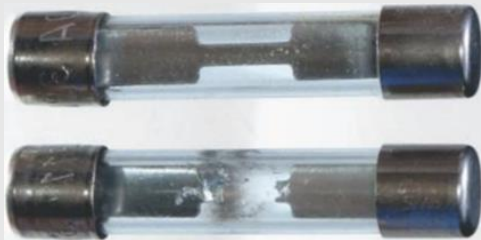
Polyfuse Summary

- **Slow**
- **Lossy – 2x regular fuse**
- **Inaccurate**
- **Each OC event increases resistance**
- **Not suitable for high temp.**
 - R increases with Temp.-
- **Resets after OC event**
- **Low Cost**
- **Can provide Safety Agency compliance**
 - UL, IEC, CSA

Common Circuit Protection

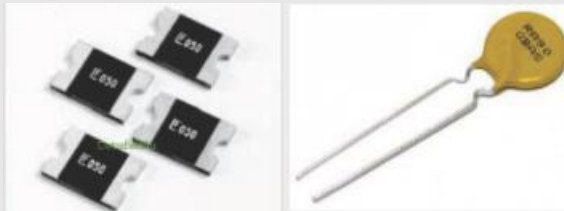
Fuses

- Physically breaks once tripped, only one time use (Not resettable)
- Fast acting / time delay trip
- System is offline until fuse is physically replaced



Polyfuse (PTC)

- Temp-based current limit
- Auto-resets after fault
- Resistance increases with temp and after each fault
- Slow response/trip after fault (Several ms)
- Time-delay trip only



Texas Instruments eFuses

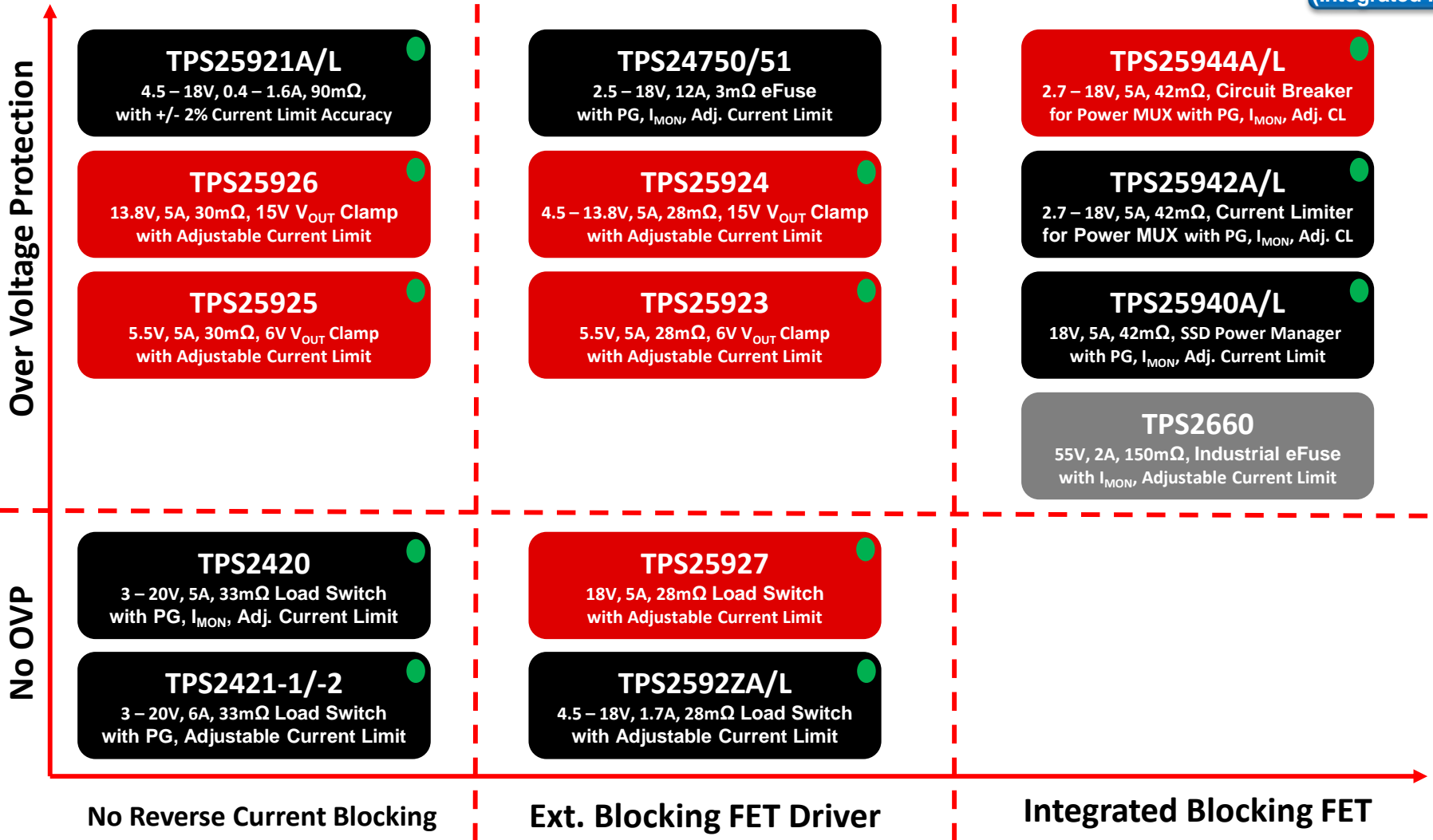
- High accuracy adjustable current limit (up to $\pm 2\%$)
- Fast trip (< 1.5 us typ)
- UL recognized devices
- Able to auto retry (PTC) or latch off (fuse) after fault
- Fault reporting, PG, IMON



eFuses (Integrated FET)

Need more? See
Parametric
Search:

eFuses
(Integrated FET)



● = UL 2367
Recognized

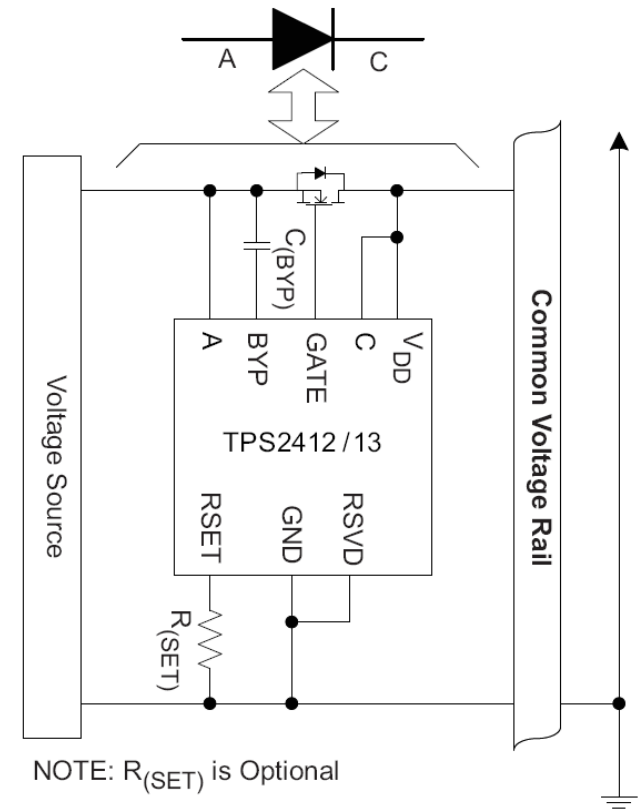
NEW EXISTING ROADMAP



Device Features/Options

ORing Control - What is it and why do it ?

- What is it ?
 - **Make a FET act like a diode**
 - No more, no less
 - A simple concept
 - A challenge to implement
- Why do it ?
 - Save Energy, \$\$\$
 - Improve PS margin

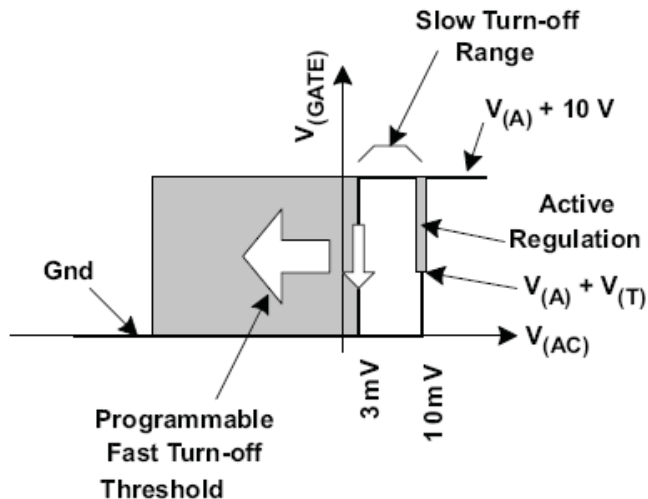


Device Features/Options

ORing Control – Linear vs. Hysteretic

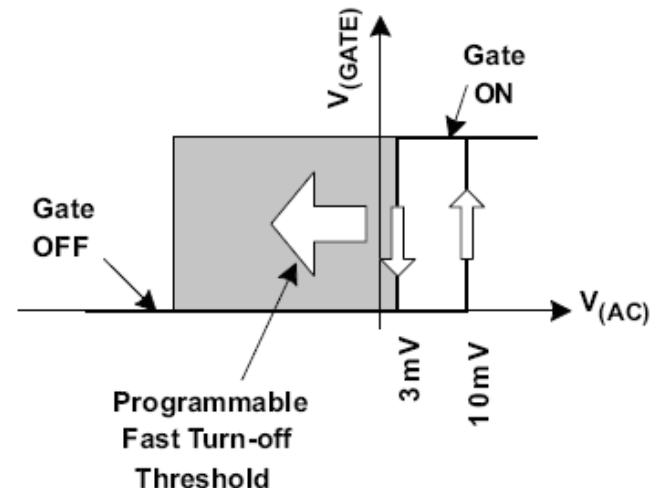
Linear Control

- Regulates V_{AC} (V_{SD}) to 10 mV
- Reverse current less likely
- May not like reactive loads



Hysteretic Control

- FET on if $V_{AC} > 10$ mV
- FET off if $V_{AC} < 3$ mV
- Fast off if V_{AC} goes negative
- Less sensitive to reactive loads
- More prone to light load oscillation



Oring Control Selection guide

Device	Description	Channels	V _{IN} Range (V)	Enable/Shutdown	UV	OV	Fault	PG	ORing Linear Gate Drive
TPS2410	ORing FET controller/MUX controller	1	0.8 to 16.5	1H	✓	✓	✓	✓	✓
TPS2411	ORing FET controller/MUX controller	1	0.8 to 16.5	1H					
TPS2412	ORing FET controller	1	0.8 to 16.5						✓
TPS2413	ORing FET controller	1	0.8 to 16.5						
TPS2419	ORing FET controller with OV/enable	1	3 to 16.5	1H		✓			
LM5050-1	Positive HV ORing controller with AUX input	1	5 to 80	L					✓
LM5050-2	Positive HV ORing controller with FET test	1	6 to 80	L			✓		✓
LM5051	Negative HV ORing controller with FET test	1	-6 to -100	L			✓		✓
TPS24740/1/2	High performance hotswap/ORing controller	1	2.5 to 18	1H	✓	✓	✓	✓	
TPS2456/A	Inrush/reverse current controller for dual sources	2	8.5 to 15	2H	✓		✓	✓	✓
TPS2358	Dual 12-V/3.3-V hotswap/ORing controller	2	8.5 to 15	2L					
TPS2359	Dual 12-V/3.3-V hotswap/ORing controller	2	8.5 to 15	Via I ² C					

Thanks You !